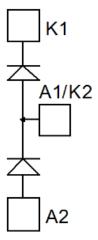
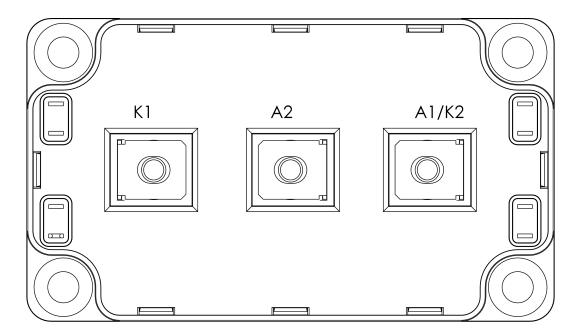


# **MSCDC600A120AG SiC Diode Phase Leg Power Module**

## 1 Product Overview

This section provides the product overview for the MSCDC600A120AG device.





All ratings at  $T_i$  = 25 °C, unless otherwise specified.

**Caution:** These devices are sensitive to electrostatic discharge. Proper handling procedures should be followed.



#### 1.1 Features

The following are key features of the MSCDC600A120AG device:

- Silicon carbide (SiC) Schottky diode
  - Zero reverse recovery
  - Zero forward recovery
  - Temperature-independent switching behavior
  - Positive temperature coefficient on VF
- Low stray inductance
- M5 power connectors
- High level of integration
- Aluminum nitride (AIN) substrate for improved thermal performance

#### 1.2 Benefits

The following are benefits of the MSCDC600A120AG device:

- Outstanding performance at high-frequency operation
- Low noise switching
- Direct mounting to heatsink (isolated package)
- Low junction-to-case thermal resistance
- RoHS compliant

### 1.3 Applications

The MSCDC600A120AG device is designed for the following applications:

- Uninterruptible power supply (UPS)
- Induction heating
- Welding equipment
- High speed rectifiers



# **2** Electrical Specifications

This section provides the electrical specifications for the MSCDC600A120AG device.

### 2.1 Absolute Maximum Ratings

The following table shows the absolute maximum ratings per diode for the MSCDC600A120AG device.

**Table 1 • Absolute Maximum Ratings** 

Symbol	Parameter		Maximum Ratings	Unit
V <sub>RRM</sub>	Repetitive peak reverse voltage		1200	V
l <sub>F</sub>	DC forward current	Tc = 85 °C	600*	Α

<sup>\*</sup> Specification of SiC device, but output current must be limited due to size of power connectors.

The following table shows the thermal and package characteristics of the MSCDC600A120AG.

**Table 2 • Thermal and Package Characteristics** 

Symbol	Characteristic			Min	Max	Unit
Visol	RMS isolation voltage, any terminal to case t =1 minute, 50 Hz/60 Hz			4000		V
Tı	Operating junction temperature range			-40	175	°C
Тлор	Recommended junction temperature under swit	ching conditions		-40	T <sub>Jmax</sub> -25	
Тѕтс	Storage temperature range			-40	125	
Tc	Operating case temperature			-40	125	
Torque	Mounting torque To hea	To heatsink	M6	3	5	N.m
		For terminals	M5	2	3.5	
Wt	Package weight				300	g

#### 2.2 Electrical Performance

The following table shows the electrical characteristics per diode of the MSCDC600A120AG.

Table 3 • Electrical Characteristics Per Diode

Symbol	Characteristic Diode forward voltage	Test Conditions	Test Conditions		Тур	Max	Unit
VF		I <sub>F</sub> = 600 A	T <sub>j</sub> = 25 °C		1.5	1.8	V
			T <sub>j</sub> = 175 °C		2.1		-
Irm	Reverse leakage current	V <sub>R</sub> = 1200 V	T <sub>j</sub> = 25 °C		0.18	2.4	mA
			T <sub>j</sub> = 175 °C		3		-
<b>Q</b> c	Total capacitive charge	V <sub>R</sub> = 600 V			2688		nC
С	Total capacitance	f = 1 MHz, V <sub>R</sub> = 400 V			2952		pF
		f = 1 MHz, V <sub>R</sub> = 8	800 V		2184		-
RthJC	Junction-to-case thermal resist	ance				0.06	°C/W



## 2.3 Performance Curves

This section shows the typical performance curves for the MSCDC600A120AG device.

Figure 1 • Maximum Transient Thermal Impedance

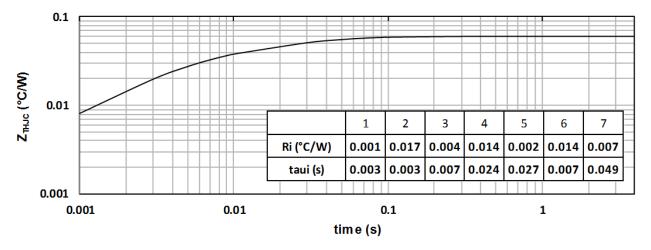


Figure 2 • Forward Current vs. Forward Voltage

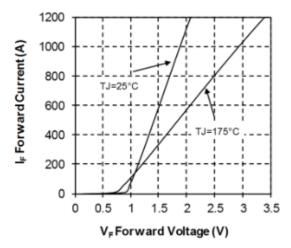
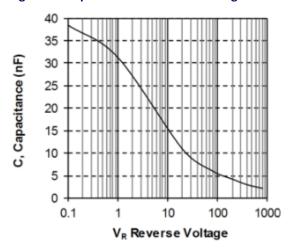


Figure 3 • Capacitance vs. Reverse Voltage





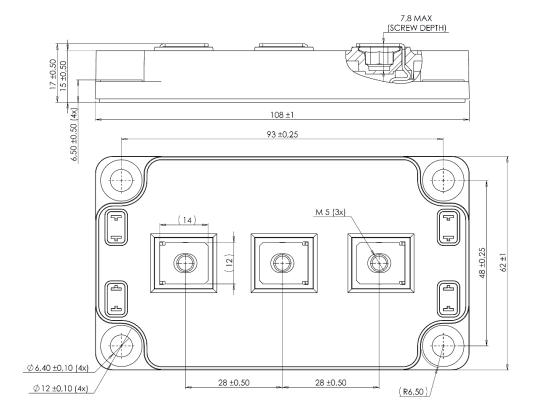
# **3** Package Specifications

This section shows the package specifications for the MSCDC600A120AG device.

## 3.1 Package Outline Drawing

The following drawing shows the package outline of the MSCDC600A120AG device. The dimensions in the following figure are in millimeters.

Figure 4 • Package Outline Drawing







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